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(54) **Title:** SEMICONDUCTOR PROCESS CHAMBER AND SEMICONDUCTOR PROCESS APPARATUS

(54) 发明名称: 半导体工艺腔室及半导体工艺设备

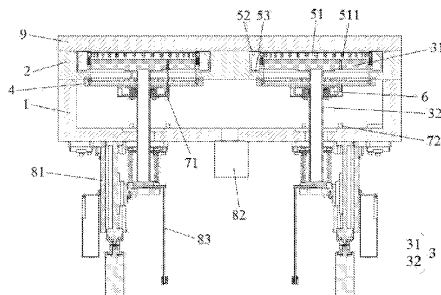


图 1

(57) **Abstract:** Provided in the present application are a semiconductor process chamber and a semiconductor process apparatus. The semiconductor process chamber comprises an outer cavity internally provided with a plurality of reaction areas, each of which is provided with a reaction cavity, a bearing device and a sealing assembly, wherein an opening is provided in a bottom end of the reaction cavity; the bearing device comprises a support shaft capable of ascending and descending and a bearing portion for bearing a wafer, the support shaft being arranged at the bottom of the bearing portion, being configured to support the bearing portion, and ascending and descending via the opening between a process position in the reaction cavity and a conveying position located below the reaction cavity; and the sealing assembly is arranged below the bearing portion and is connected to the bearing device, the support shaft penetrates the sealing assembly, the sealing assembly is configured to ascend and descend along with the ascending and descending of the support shaft, and when the support shaft supports the bearing portion to ascend to the process position, the sealing assembly comes into contact with the bottom end of the reaction cavity, so as to seal the opening. The semiconductor process chamber and the semiconductor process apparatus provided in the present invention can improve the sealing stability of the sealing assembly, thereby improving the usage stability of the semiconductor process chamber and the semiconductor process apparatus.

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本国际公布:

— 包括国际检索报告(条约第21条(3))。

(57) 摘要: 本申请提供一种半导体工艺腔室及半导体工艺设备, 半导体工艺腔室包括内部具有多个反应区域的外腔体, 每一反应区域设有反应腔体、承载装置和密封组件; 反应腔体底端具有开口; 承载装置包括可升降的支撑轴和用于承载晶圆的承载部, 支撑轴设在承载部底部, 用于支撑承载部, 并经开口在反应腔体内的工艺位和位于反应腔体下方的传输位之间升降; 密封组件设在承载部下方并与承载装置连接, 且支撑轴贯穿密封组件, 密封组件用于随支撑轴升降而升降, 且在支撑轴支撑承载部上升至工艺位时与反应腔体底端接触, 以密封开口。本发明提供的半导体工艺腔室及半导体工艺设备能够提高密封组件的密封稳定性, 并能够提高半导体工艺腔室及半导体工艺设备的使用稳定性。